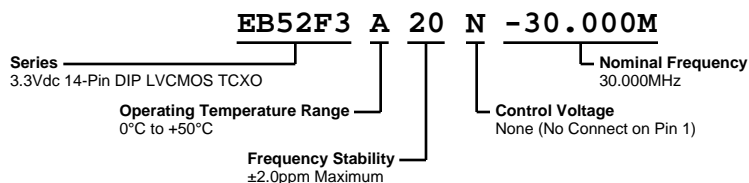


# EB52F3A20N-30.000M



## ELECTRICAL SPECIFICATIONS

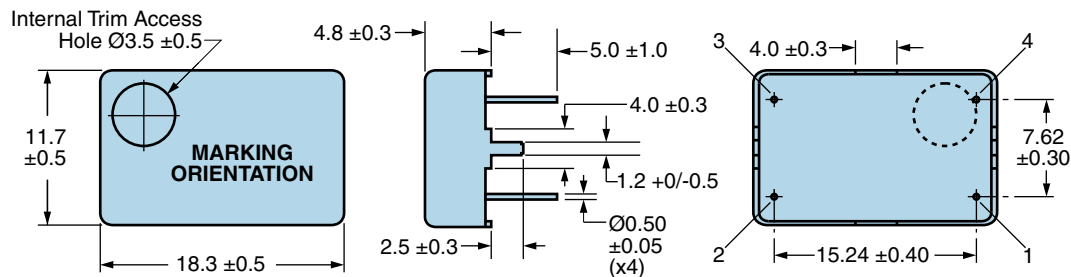
Nominal Frequency	30.000MHz
Frequency Stability	±2.0ppm Maximum (Inclusive of Operating Temperature Range)
Frequency Stability vs. Input Voltage	±0.3ppm Maximum (±5%)
Aging at 25°C	±1ppm/Year Maximum
Frequency Stability vs. Load	±0.2ppm Maximum (±2pF)
Operating Temperature Range	0°C to +50°C
Supply Voltage	3.3Vdc ±5%
Input Current	20mA Maximum
Output Voltage Logic High (Voh)	90% of Vdd Minimum
Output Voltage Logic Low (Vol)	10% of Vdd Maximum
Rise/Fall Time	10nSec Maximum (Measured at 20% to 80% of waveform)
Duty Cycle	50% ±10% (Measured at 50% of waveform)
Load Drive Capability	15pF Maximum
Output Logic Type	CMOS
Control Voltage	None (No Connect on Pin 1)
Internal Trim	±3ppm Minimum (Top of Can)
Modulation Bandwidth	10kHz Minimum (Measured at -3dB with a Control Voltage of 1.65Vdc)
Input Impedance	10kOhms Typical
Phase Noise	-70dBc at 10Hz Offset, -100dBc at 100Hz Offset, -130dBc at 1kHz Offset, -140dBc at 10kHz Offset, -145dBc at 100kHz Offset
Storage Temperature Range	-40°C to +85°C

## ENVIRONMENTAL & MECHANICAL SPECIFICATIONS

Fine Leak Test	MIL-STD-883, Method 1014 Condition A (Internal Crystal Only)
Gross Leak Test	MIL-STD-883, Method 1014 Condition C (Internal Crystal Only)
Lead Integrity	MIL-STD-883, Method 2004
Mechanical Shock	MIL-STD-202, Method 213 Condition C
Resistance to Soldering Heat	MIL-STD-202, Method 210
Resistance to Solvents	MIL-STD-202, Method 215
Solderability	MIL-STD-883, Method 2003
Temperature Cycling	MIL-STD-883, Method 1010
Vibration	MIL-STD-883, Method 2007 Condition A

# EB52F3A20N-30.000M

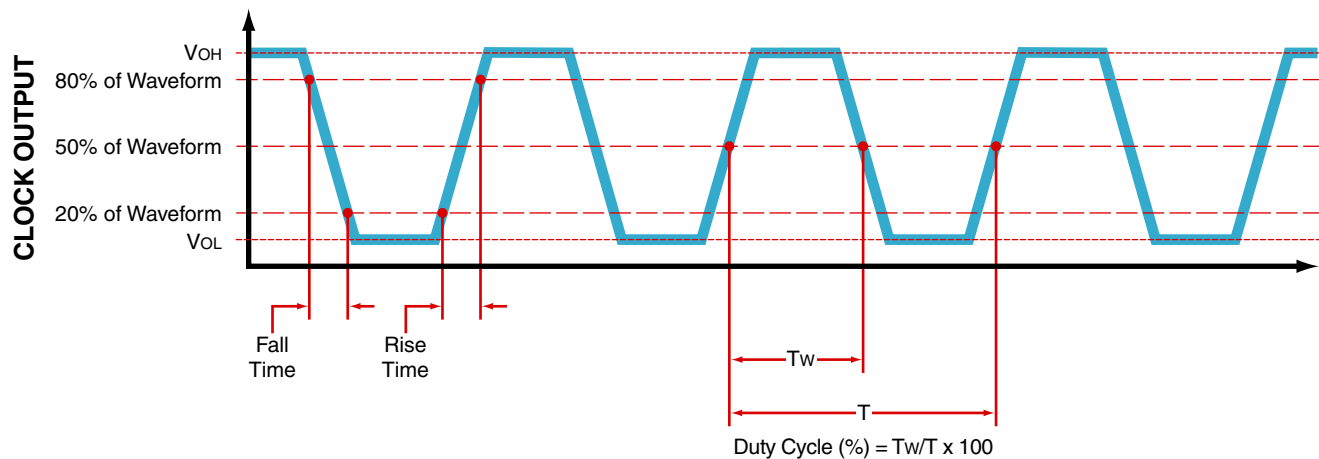
## MECHANICAL DIMENSIONS (all dimensions in millimeters)



PIN	CONNECTION
1	No Connect
2	Case/Ground
3	Output
4	Supply Voltage

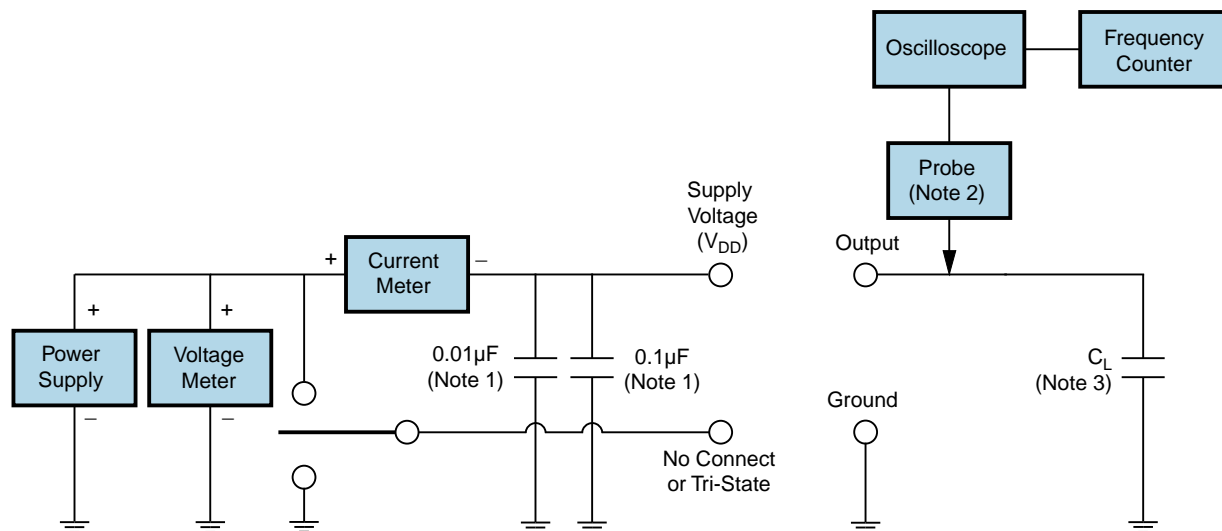
LINE	MARKING
1	<b>ECLIPTEK</b>
2	<b>30.000M</b>
3	<b>XXYYZZ</b> XX=Ecliptek Manufacturing Code Y=Last Digit of the Year ZZ=Week of the Year

## OUTPUT WAVEFORM



# EB52F3A20N-30.000M

## Test Circuit for CMOS Output

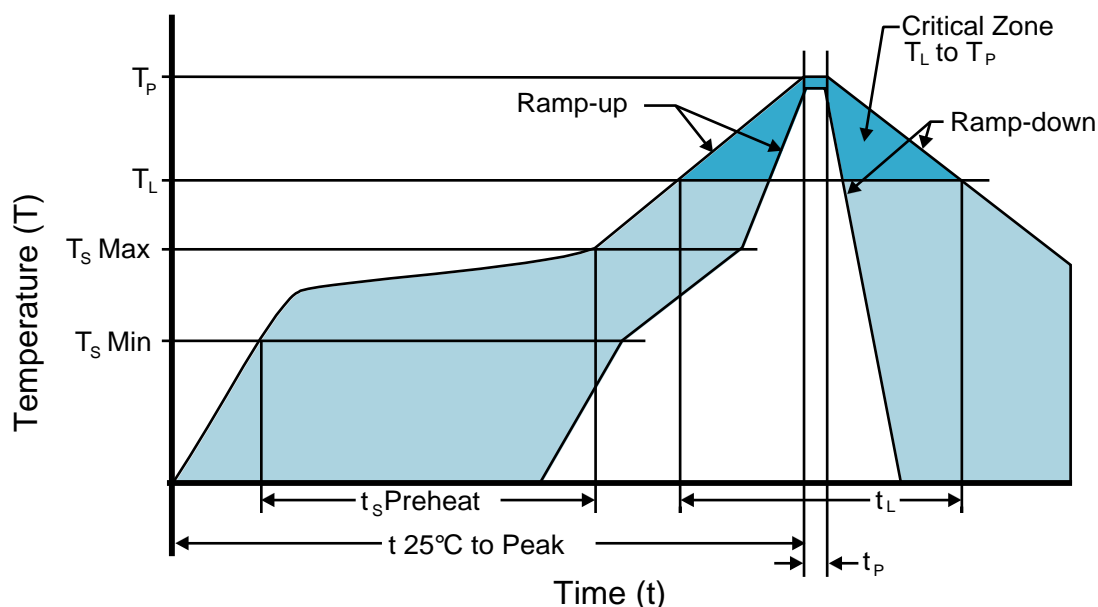


Note 1: An external 0.1µF low frequency tantalum bypass capacitor in parallel with a 0.01µF high frequency ceramic bypass capacitor close to the package ground and  $V_{DD}$  pin is required.

Note 2: A low capacitance (<12pF), 10X attenuation factor, high impedance (>10Mohms), and high bandwidth (>300MHz) passive probe is recommended.

Note 3: Capacitance value  $C_L$  includes sum of all probe and fixture capacitance.

## Recommended Solder Reflow Methods



### Low Temperature Solder Bath (Wave Solder)

$T_S$  MAX to  $T_L$  (Ramp-up Rate) 5°C/second Maximum

#### Preheat

- Temperature Minimum ( $T_S$  MIN) N/A
- Temperature Typical ( $T_S$  TYP) 150°C
- Temperature Maximum ( $T_S$  MAX) N/A
- Time ( $t_s$  MIN) 30 - 60 Seconds

Ramp-up Rate ( $T_L$  to  $T_P$ ) 5°C/second Maximum

#### Time Maintained Above:

- Temperature ( $T_L$ ) 150°C
- Time ( $t_L$ ) 200 Seconds Maximum

Peak Temperature ( $T_P$ ) 245°C Maximum

Target Peak Temperature ( $T_P$  Target) 245°C Maximum 1 Time / 235°C Maximum 2 Times

Time within 5°C of actual peak ( $t_p$ ) 5 seconds Maximum 1 Time / 15 seconds Maximum 2 Times

Ramp-down Rate 5°C/second Maximum

Time 25°C to Peak Temperature (t) N/A

Moisture Sensitivity Level Level 1

### Low Temperature Manual Soldering

185°C Maximum for 10 seconds Maximum, 2 times Maximum.

### High Temperature Manual Soldering

260°C Maximum for 5 seconds Maximum, 2 times Maximum.

### Low Temperature Solder Bath (Wave Solder) Note 1

Device is non-hermetic; Post reflow aqueous wash is not recommended

### Low Temperature Solder Bath (Wave Solder) Note 2

Temperatures shown are applied to back of PCB board and device leads only.